Notice of Allowability	Application No.	Applicant(s)	
	10/650,089	SEO ET AL.	
	Examiner	Art Unit	لهم
	Hoai v Pham	2814	(**
The MAILING DATE of this communication appeal claims being allowable, PROSECUTION ON THE MERITS IS (herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT Right	OR REMAINS) CLOSED in this apport of the communication GHTS. This application is subject to	plication. If not include n will be mailed in due o	d course. THIS
1. This communication is responsive to <u>7/6/2004</u> .			
2. ☑ The allowed claim(s) is/are <u>1-10 and 13</u> .			
3. $igotimes$ The drawings filed on <u>28 August 2003</u> are accepted by the	Examiner.		
4. Acknowledgment is made of a claim for foreign priority un a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" of noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give (a) including changes required by the Notice of Draftsperson 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the company of the proper of the deposent attached Examiner's comment regarding REQUIREMENT in the company of the priority of the deposent attached Examiner's comment regarding REQUIREMENT in the company of the deposent attached Examiner's comment regarding REQUIREMENT in the company of the priority of the	been received. been received in Application No cuments have been received in this of this communication to file a reply ENT of this application. Itted. Note the attached EXAMINER is reason(s) why the oath or declara it be submitted. It be submitted. It is application on the Comment or in the Comment or in the Comment of the declaration of the declaration of the declaration of the comment of the Comment or in the Comment of the declaration of	national stage applicational stage application of the front (not the d). national stage application is deficient.	uirements OTICE OF back) of
Attachment(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO-1449 or PTO/SB/0: Paper No./Mail Date 8/28/03 4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	5. Notice of Informal F 6. Interview Summary Paper No./Mail Da 7. Examiner's Amendr 8. Examiner's Stateme 9. Other	(PTO-413), te ment/Comment	·

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DETAILED ACTION

Election/Restrictions

1. Applicant's election of claims 1-10 and 13 in the reply filed on 07/06/2004 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Examiner's amendment

- 2. An examiner's amendment to the record appears below. Should the changes and/or additions be unacceptable to applicant, an amendment may be filed as provided by 37 CFR 1.312. To ensure consideration of such an amendment, it MUST be submitted no later than the payment of the issue fee.
- 3. This application is in condition for allowance except for the presence of 11-12 and 14 non-elected without traverse. Accordingly, claims 11-12 and 14 have been cancelled.
- 4. The application has been amended as follows:

In the claims:

Cancel 11-12 and 14.

In the specification:

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Change the title to: --A METHOD OF MANUFACTURING THE
SEMICONDUCTOR DEVICE INTENDED TO PREVENT A LEAKAGE CURRENT
FROM OCCURING DUE TO A GATE INDUCED DRAIN LEAKAGE EFFECT---.

Allowable Subject Matter

- 5. Claims 1-10 and 13 are allowed.
- 6. The following is an examiner's statement of reasons for allowance: the prior of record fails to disclose forming a high concentration source/drain regions of a PMOS by using the first dielectric film formed on upper pads of a gate pattern and a gate spacer of a PMOS transistor as an implant mask, while having the characteristics as recites in claims 1, 5, 6 and 13.
- 7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hoai v Pham whose telephone number is 571-272-1715. The examiner can normally be reached on M-F.
- 8. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael M Fahmy can be reached on 571-272-1705. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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9. Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Hoai Pham

Patent Examiner